

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

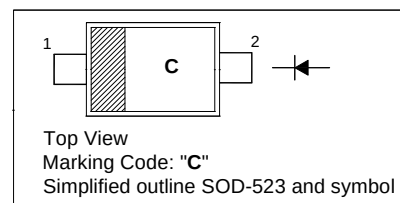
for low current rectification and high speed
switching applications

Features

- Extremely small surface mounting type

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

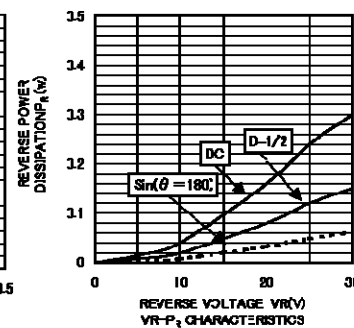
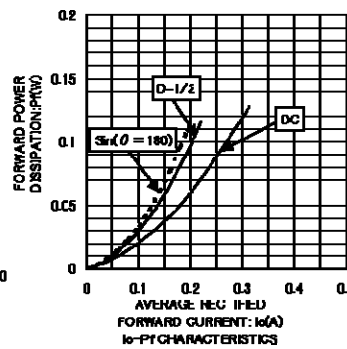
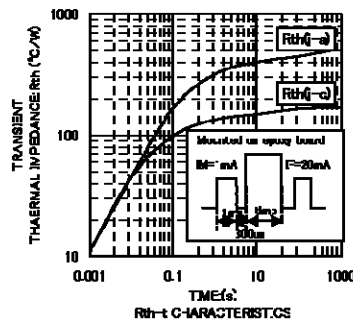
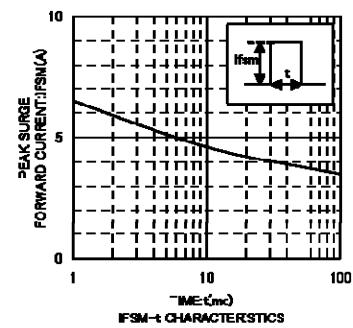
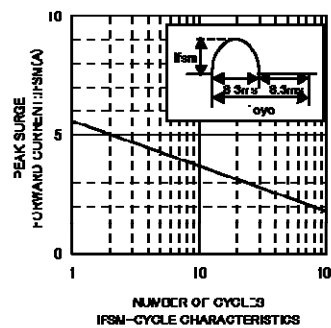
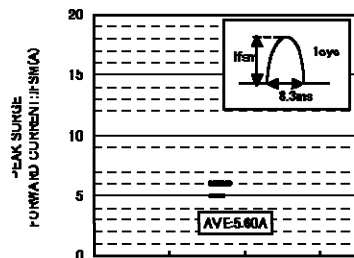
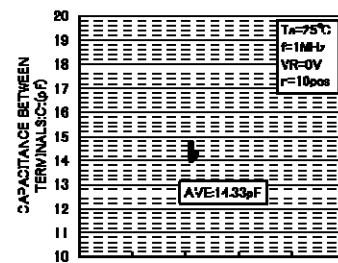
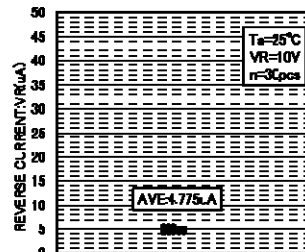
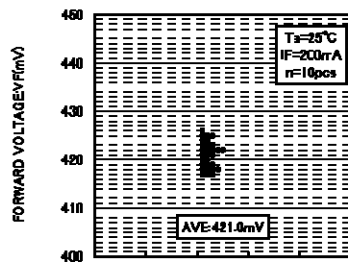
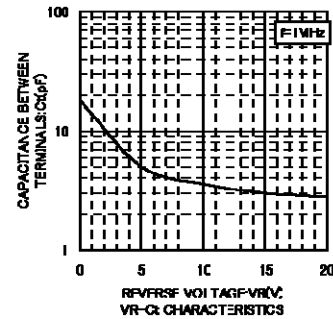
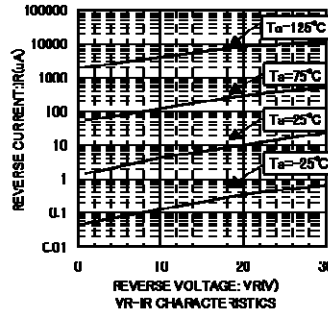
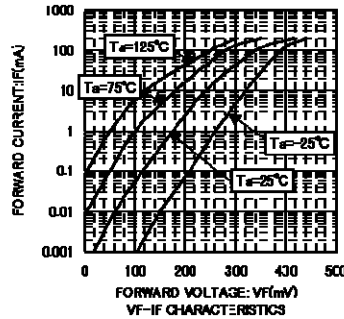


Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

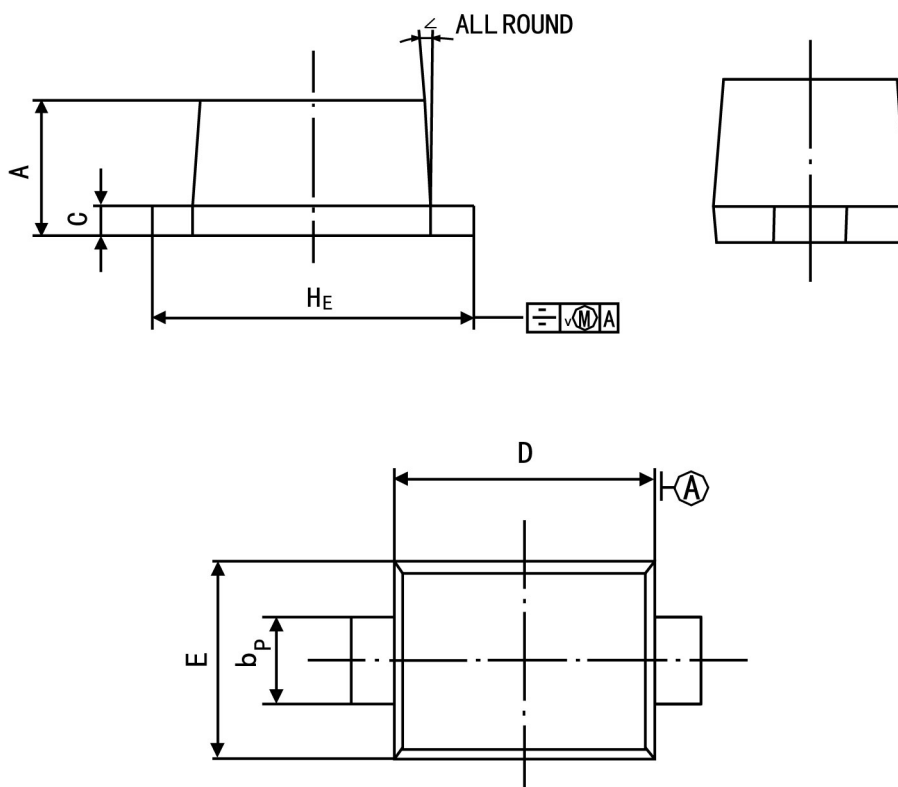
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	0.5	V
Reverse Current at $V_R = 10\text{ V}$	I_R	30	μA



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
bp	0.30	0.40
C	0.100	0.14
D	1.15	1.25
E	0.75	0.85
HE	1.50	1.70
V	—	0.10
∠	—	5°